

Title (en)  
MEASURING A DIFFRACTING STRUCTURE, BROADBAND, POLARIZED, ELLIPSOMETRIC, AND AN UNDERLYING STRUCTURE

Title (de)  
MESSUNG EINER DIFRAKTIONSSTRUKTUR, BREITBANDIG, POLARISIEREND UND ELLIPSOMETRISCH UND EINE UNTERLIEGENDE STRUKTUR

Title (fr)  
MESURE D'UNE STRUCTURE DIFFRACTANTE, LARGE BANDE, POLARISEE, ELLIPSOMETRIQUE ET D'UNE STRUCTURE SOUS-JACENTE

Publication  
**EP 1073876 B1 20041229 (EN)**

Application  
**EP 99937981 A 19990225**

Priority  
• US 9904053 W 19990225  
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Abstract (en)  
[origin: WO9945340A1] Before the diffraction from a diffracting structure on a semiconductor wafer is measured, where necessary, the film thickness and index of refraction of the films underneath the structure are first measured using spectroscopic reflectometry or spectroscopic ellipsometry. A rigorous model is then used to calculate intensity or ellipsometric signatures of the diffracting structure. The diffracting structure is then measured using a spectroscopic scatterometer using polarized and broadband radiation to obtain an intensity or ellipsometric signature of the diffracting structure. Such signature is then matched with the signatures in the database to determine the grating shape parameters of the structure.

IPC 1-7  
**G01B 11/02**; **H01L 21/66**; **G03F 7/20**

IPC 8 full level  
**G01B 11/02** (2006.01); **G01B 11/06** (2006.01); **G01N 21/21** (2006.01); **G01N 21/27** (2006.01); **G01N 21/95** (2006.01); **G01N 21/956** (2006.01); **G03F 7/20** (2006.01); **H01L 21/66** (2006.01)

CPC (source: EP US)  
**G01B 11/0641** (2013.01 - EP US); **G01N 21/211** (2013.01 - EP US); **G01N 21/4788** (2013.01 - EP US); **G01N 21/55** (2013.01 - EP US); **G01N 21/9501** (2013.01 - EP US); **G01N 21/956** (2013.01 - EP US); **G01N 21/95607** (2013.01 - EP US); **G03F 7/70491** (2013.01 - EP US); **G03F 7/70616** (2013.01 - EP US); **G03F 7/70625** (2013.01 - EP US); **G01N 2021/213** (2013.01 - EP US); **G01N 2021/556** (2013.01 - EP US); **G01N 2021/95615** (2013.01 - EP US); **H01L 22/12** (2013.01 - EP US); **H01L 2924/0002** (2013.01 - EP US)

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**WO 9945340 A1 19990910**; AU 3310999 A 19990920; DE 69922942 D1 20050203; DE 69922942 T2 20060330; EP 1073876 A1 20010207; EP 1073876 B1 20041229; EP 1508772 A1 20050223; EP 1508772 B1 20130821; JP 2002506198 A 20020226; JP 2010066268 A 20100325; JP 2010133941 A 20100617; JP 2010133942 A 20100617; JP 2010281822 A 20101216; JP 2013083659 A 20130509; JP 4633254 B2 20110216; JP 4643737 B2 20110302; JP 5102329 B2 20121219; JP 5249169 B2 20130731; JP 5563803 B2 20140730; US 2002033945 A1 20020321; US 2003058443 A1 20030327; US 2007091327 A1 20070426; US 2010165340 A1 20100701; US 2011125458 A1 20110526; US 6483580 B1 20021119; US 6590656 B2 20030708; US 7173699 B2 20070206; US 7859659 B2 20101228; US 7898661 B2 20110301

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